

ABSTRACT OF THE DISCLOSURE

A gate electrode is formed on a semiconductor substrate with a gate insulating film interposed therebetween. A channel region composed of a first-conductivity-type semiconductor layer is formed in a region of a surface portion of the semiconductor substrate located below the gate electrode. Source/drain regions each composed of a second-conductivity-type impurity layer are formed in regions of the surface portion of the semiconductor substrate located on both sides of the gate electrode. Second-conductivity-type extension regions are formed between the channel region and respective upper portion of the source/drain regions in contact relation with the source/drain regions. First-conductivity-type pocket regions are formed between the channel region and respective lower portion of the source/drain regions in contact relation with the source/drain regions and in spaced relation to the gate insulating film.